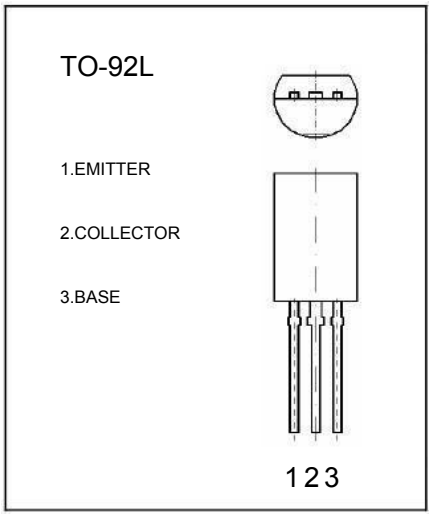
TO-92L Plastic-Encapsulate Transistors

A928A TRANSISTOR (PNP)



FEATURES

Low collector to emitter saturation voltage $V_{CE(sat)}$.
Complementary pair with C2328A

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter			Units
V_{CBO}	Collector-Base Voltage		-30	V
V_{CEO}	Collector-Emitter Voltage		-30	V
V_{EBO}	Emitter-Base Voltage	-5		V
I_C	Collector Current –Continuous	-2		A
P_C	Collector Power Dissipation	1		W
T_J	Junction Temperature	+150		℃
T_{stg}	Storage Temperature	-55-+150		℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA, I_E=0	-30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-10mA, I_B=0	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-1mA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-30V, I_E=0			-100	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V， I_C=0			-100	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-2V, I_C=-500mA	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-1.5A, I_B=-30mA			-2.0	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-500mA, V_{CE}=-2V			-1.0	V
Transition frequency	f_T	V_{CE}=-2V, I_C=-500mA		120		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	Q	Y
Range	100-200	160--320